

HCM2G0080120K

1200V N-Channel Silicon Carbide Power MOSFET

V_{DS}	=	1200 V
$R_{DS(on)}$	=	75 mΩ
I_D	=	42 A

Features

Optimized package with separate driver source pin
Low on-resistance with high junction temperature
High-speed switching with low capacitances
Fast intrinsic diode with low reverse recovery (Q_{rr})
Easy to parallel
RoHS compliant

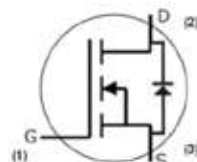
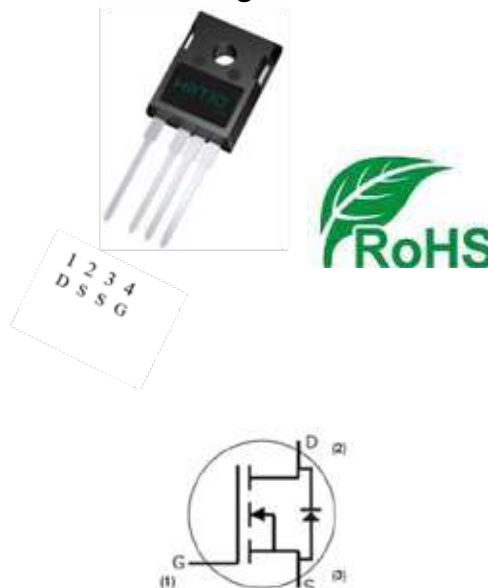
Benefits

Higher System Efficiency
Reduce cooling requirements
Increased power density
Enabling higher frequency
Minimize gate ringing
Reduction of system complexity and cost

Applications

Switch Mode Power Supplies
DC/DC converters
Solar Inverters
Battery Chargers
Motor Drives

Package



Part Number	Package	Marking
HCM2G0080120K	TO-247-4	HCM2G0080120K

Maximum Ratings, at $T_J = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain-Source Breakdown Voltage	1200	V	$V_{GS} = 0\text{ V}$, $I_D = 100\text{ }\mu\text{A}$	
I_D	Continuous Drain Current	42	A	$V_{GS} = 20\text{ V}$, $T_C = 25^{\circ}\text{C}$	Fig. 18
		30	A	$V_{GS} = 20\text{ V}$, $T_C = 100^{\circ}\text{C}$	
$I_{D(pluse)}$	Pulsed Drain Current	84	A	Pulsed width t_p limited by T_{Jmax}	Fig. 21
P_D	Power Dissipation	208	W	$T_C = 25^{\circ}\text{C}$	Fig. 19
$V_{GS,op}$	Recommend Gate Source Voltage (static)	-5/+20	V		
V_{GSmax}	Maximum Gate Source Voltage (dynamic)	-10/+25	V	AC ($f > 1\text{Hz}$)	
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$		
T_L	Soldering Temperature	260	$^{\circ}\text{C}$		

Electrical Characteristics, at $T_J = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
Static							
BV _{DS}	Drain-Source Breakdown Voltag	1200	--	--	V	V _{GS} = 0 V, I _D = 100 μA	
I _{DSS}	Zero Gate Voltage Drain Current	--	1	100	μA	V _{DS} = 1200 V, V _{GS} = 0 V	
I _{GSS}	Gate-Source Leakage Current	--	10	250	nA	V _{GS} = 20 V	
V _{GS(th)}	Gate-Source Threshold Voltage	2	2.7	4	V	I _D = 5 mA, V _{GS} = V _{DS}	Fig. 11
		--	2.0	--	V	I _D = 5 mA, V _{GS} = V _{DS} , T _J = 175 °C	
R _{DS(on)}	Drain-Source On-Resistance	--	75	100	mΩ	V _{GS} = 20 V, I _D = 20 A	Fig. 7
		--	85	--	mΩ	V _{GS} = 18 V, I _D = 20 A	
		--	117	--	mΩ	V _{GS} = 15 V, I _D = 20 A	
		--	119	--	mΩ	V _{GS} = 20 V, I _D = 20 A, T _J = 175 °C	
		--	124	--	mΩ	V _{GS} = 18 V, I _D = 20 A, T _J = 175 °C	
		--	155	--	mΩ	V _{GS} = 15 V, I _D = 20 A, T _J = 175 °C	
Dynamic							
C _{iss}	Input Capacitance	--	1128	--	pF	V _{GS} = 0 V, V _{DS} = 1000 V f = 1.0 MHz, V _{AC} = 25 mV	Fig. 17
C _{oss}	Output Capacitance	--	86	--			
C _{rss}	Reverse Transfer Capacitance	-	5	--			
E _{OSS}	C _{OSS} Stored Energy	--	44	--	μJ		Fig. 16
Q _g	Total Gate Charge	--	52	--	nC	V _{DS} = 800 V	Fig. 12
Q _{gs}	Gate-Source Charge	--	17	--		I _D = 20 A	
Q _{gd}	Gate-Drain Charge	--	15	--		V _{GS} = -5/+20 V	
t _{d(on)}	Turn-on Delay Time	--	35	--	ns	V _{DS} = 800 V	
t _r	Turn-on Rise Time	--	16	--		V _{GS} = -5/+20 V	
t _{d(off)}	Turn-off Delay Time	--	43	--		I _D = 20 A	
t _f	Turn-off Fall Time	--	12	--		R _{G(ext)} = 2.5 Ω	
R _{G(int)}	Internal Gate Resistance	--	4.0	--	Ω	f = 1.0 MHz, V _{AC} = 25 mV	

Body Diode Characteristics, at $T_J = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
I_S	Continuous Diode Forward Current	--	--	42	A		
$I_{S(pluse)}$	Diode pulse Current	--	--	84	A	Pulse width t_P limited by T_{Jmax}	
V_{SD}	Diode Forward Voltage	--	4.0	--	V	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}$	Fig. 8, 9, 10
		--	3.8	--	V	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}, T_J = 175^\circ\text{C}$	
t_{rr}	Reverse Recovery Time	--	26	--	ns	$I_S = 20\text{ A}, V_{DS} = 800\text{ V}$ $V_{GS} = -5\text{ V}$ $di/dt = 2100\text{ A/us}$	
Q_{rr}	Reverse Recovery Charge	-	163	--	nC		
I_{rrm}	Peak Reverse Recovery Current	--	12	--	A		

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	/	0.68	/	$^\circ\text{C/W}$	Fig. 20

Typical Performance

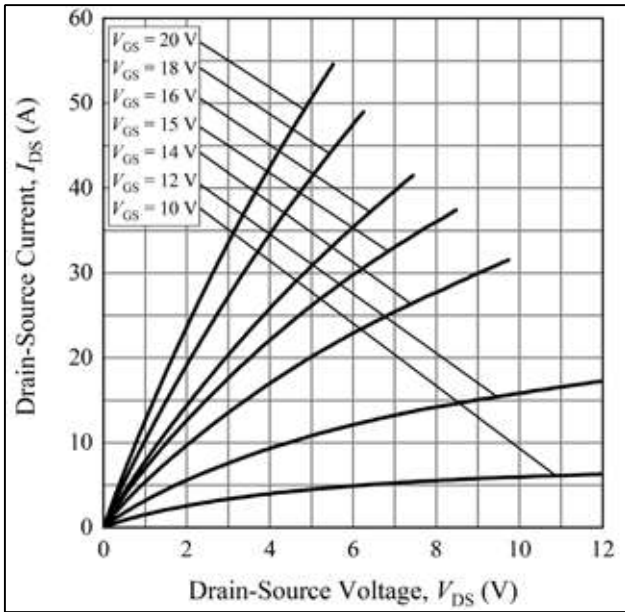


Figure 1: Typical Output Characteristics at $T_J = -55\text{ }^{\circ}\text{C}$

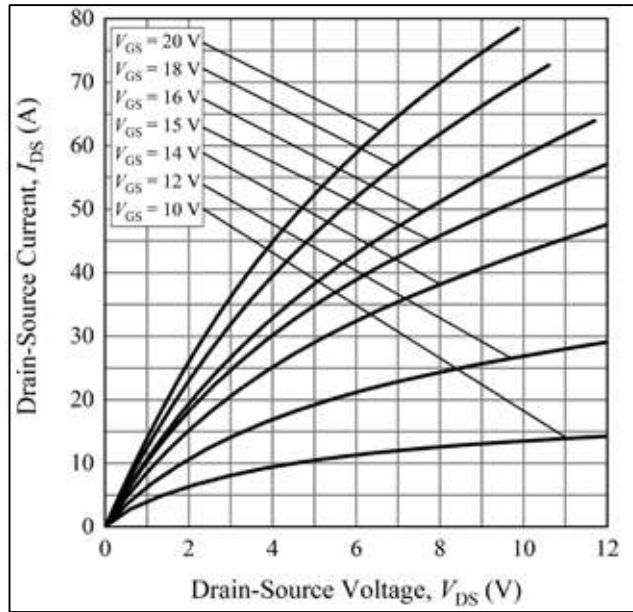


Figure 2: Typical Output Characteristics at $T_J = 25\text{ }^{\circ}\text{C}$

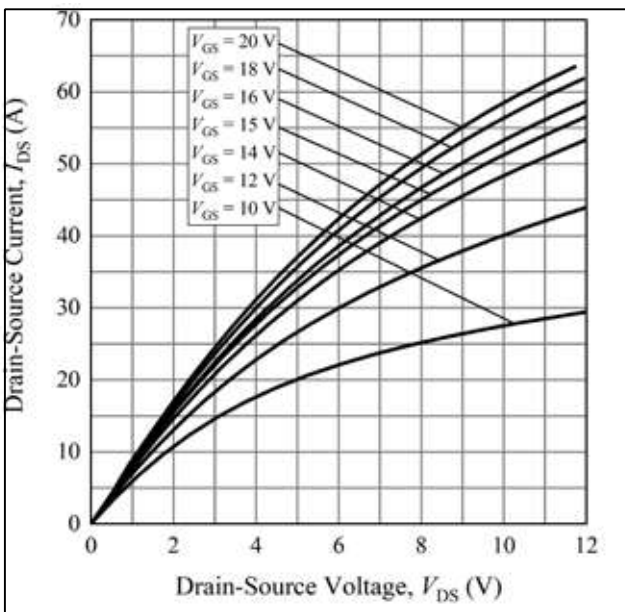


Figure 3: Typical Output Characteristics at $T_J = 175\text{ }^{\circ}\text{C}$

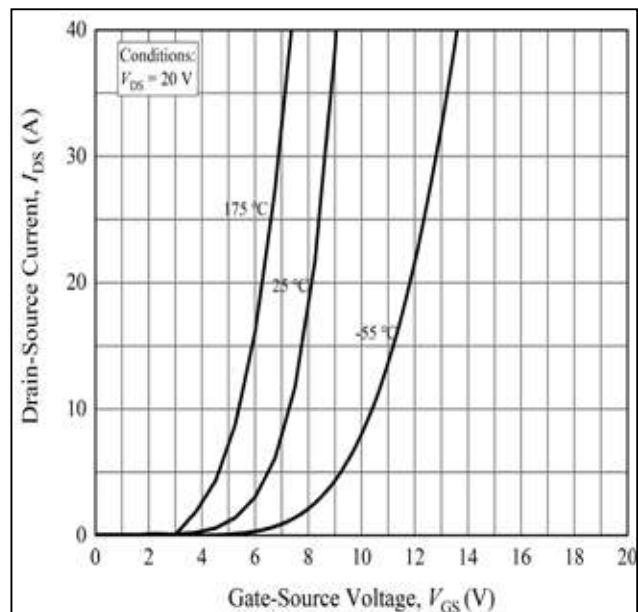


Figure 4: Typical Transfer Characteristics for Various Temperature

Typical Performance

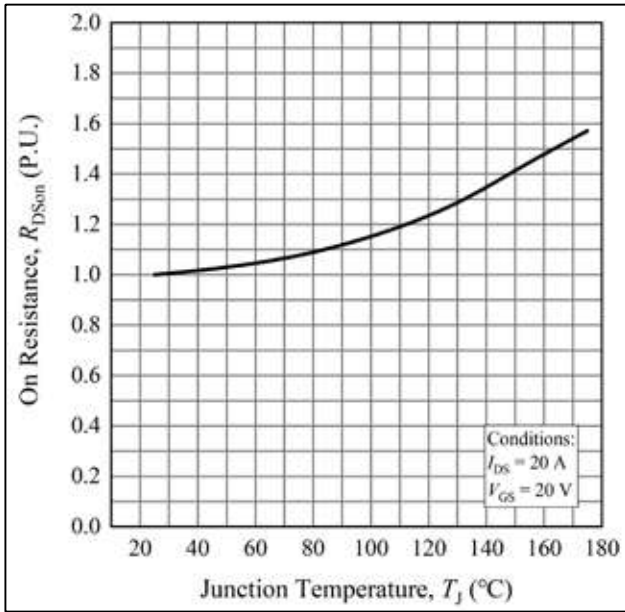


Figure 5: Normalized On-Resistance vs. Temperature

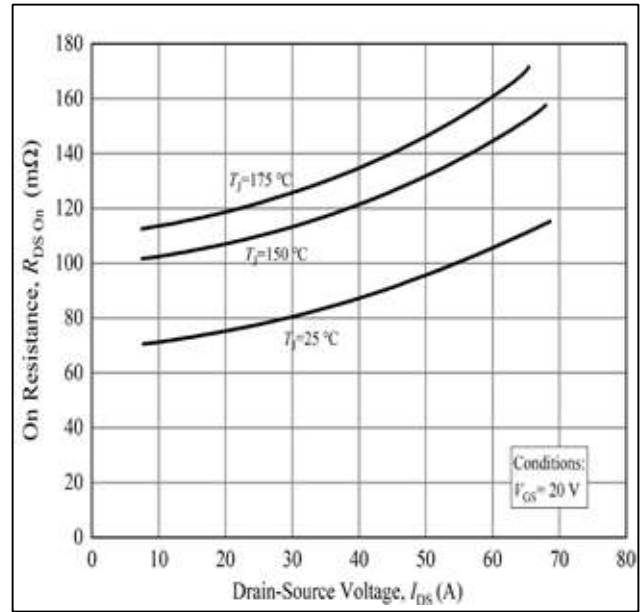


Figure 6: On-Resistance vs. Drain Current for Gate Various Temperatures

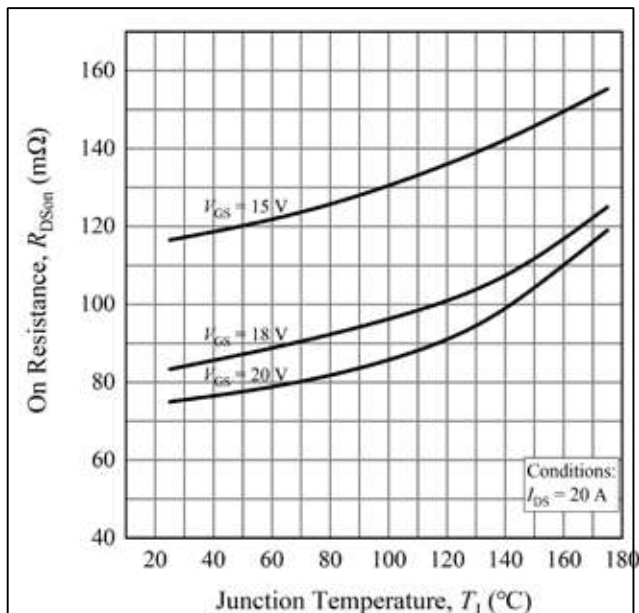


Figure 7: On-Resistance vs. Temperature for Various Voltage

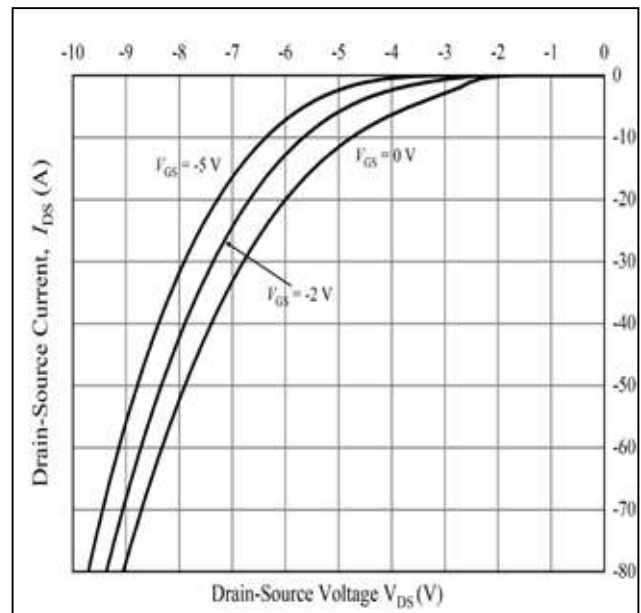


Figure 8: Typical Body Diode Characteristics at $T_J = -55\text{ }^{\circ}\text{C}$

Typical Performance

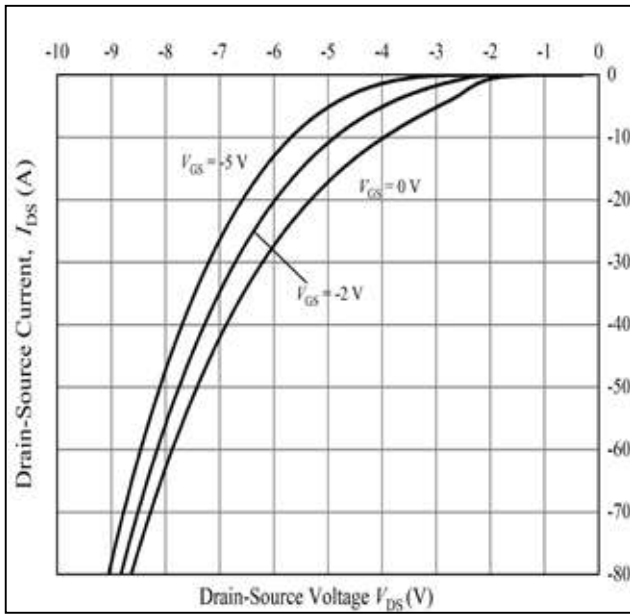


Figure 9: Typical Body Diode Characteristics at $T_J = 25\text{ }^{\circ}\text{C}$

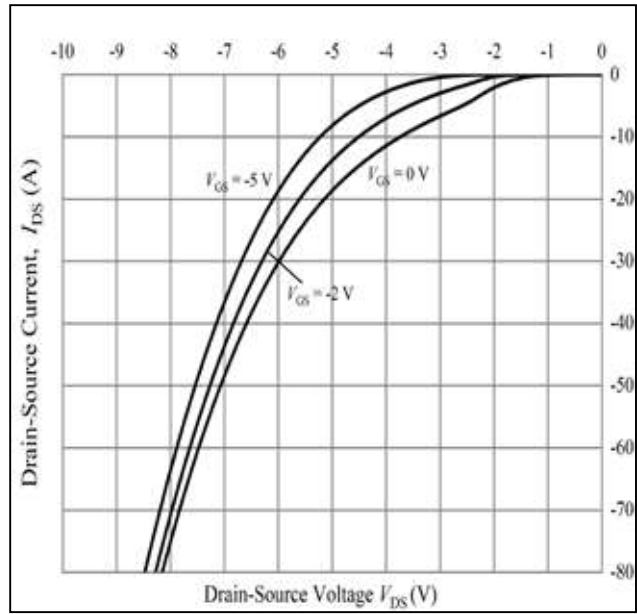


Figure 10: Typical Body Diode Characteristics at $T_J = 175\text{ }^{\circ}\text{C}$

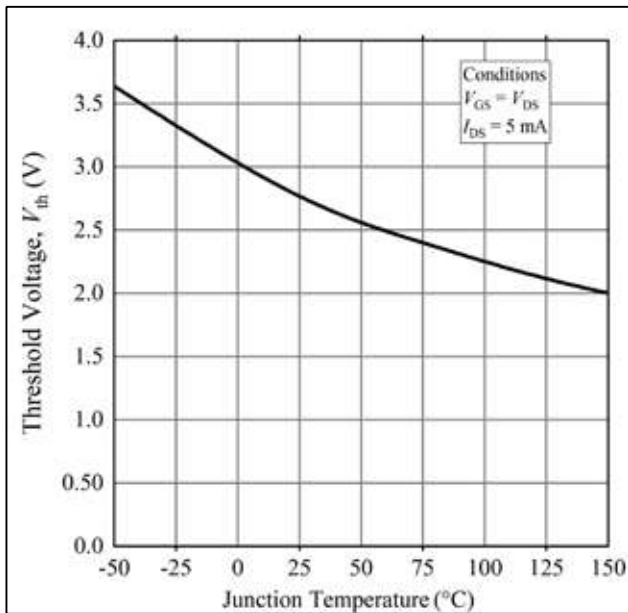


Figure 11: Typical Threshold Voltage vs. Temperature

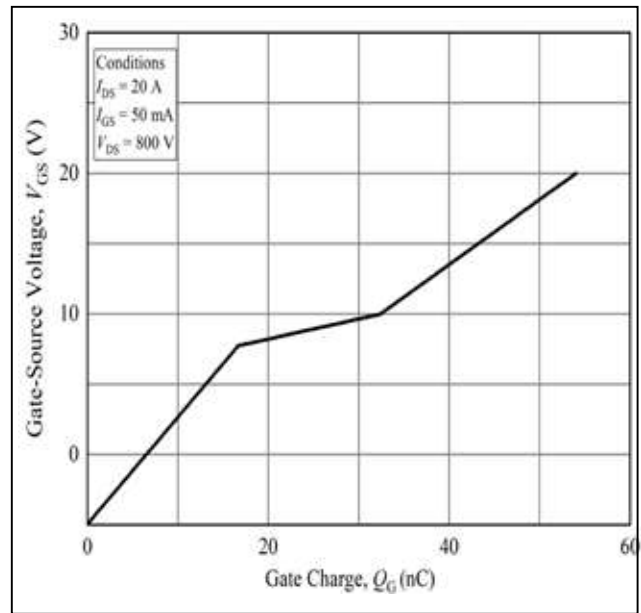


Figure 12: Typical Gate Charge Characteristics at $T_J = 25\text{ }^{\circ}\text{C}$

Typical Performance

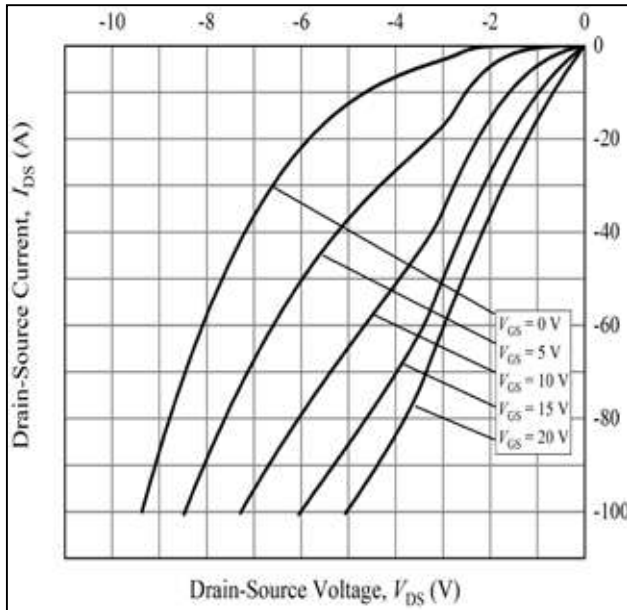


Figure 13: Typical 3rd Quadrant Characteristics
at $T_J = -55\text{ }^{\circ}\text{C}$

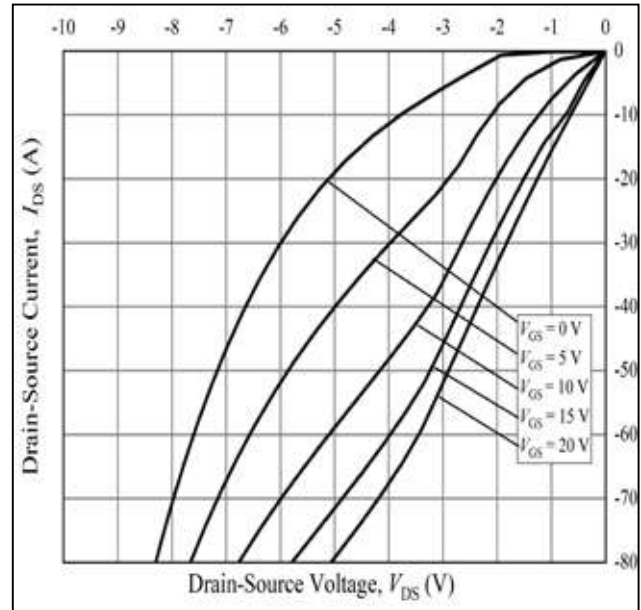


Figure 14: Typical 3rd Quadrant Characteristics at
 $T_J = 25\text{ }^{\circ}\text{C}$

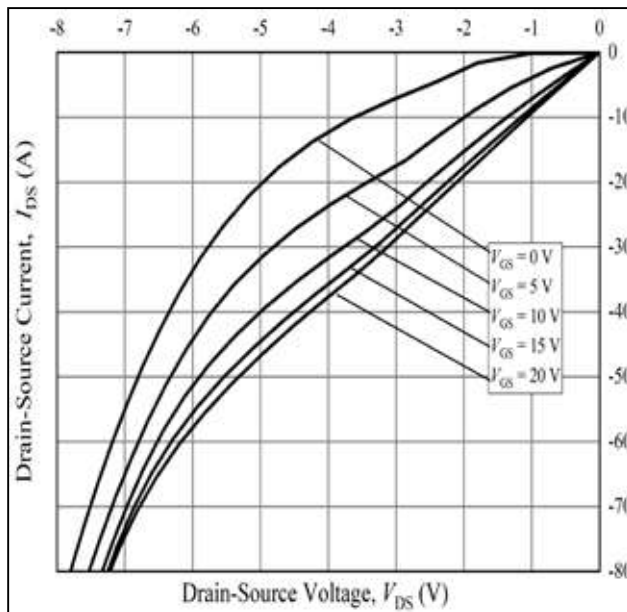


Figure 15: Typical 3rd Quadrant Characteristics
at $T_J = 175\text{ }^{\circ}\text{C}$

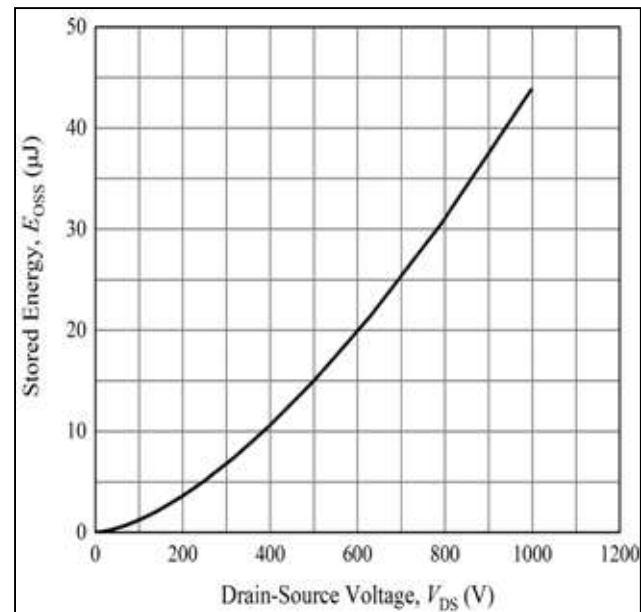


Figure 16: Typical Output Capacitor Stored Energy

Typical Performance

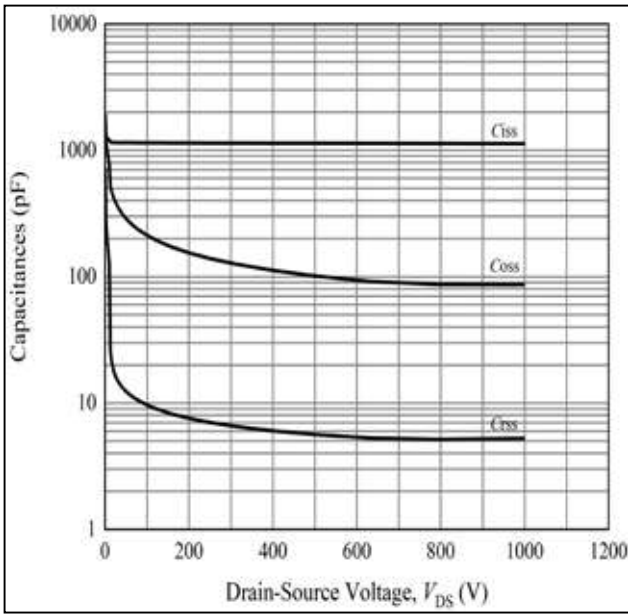


Figure 17: Typical Capacitances vs. Drain-Source Voltage

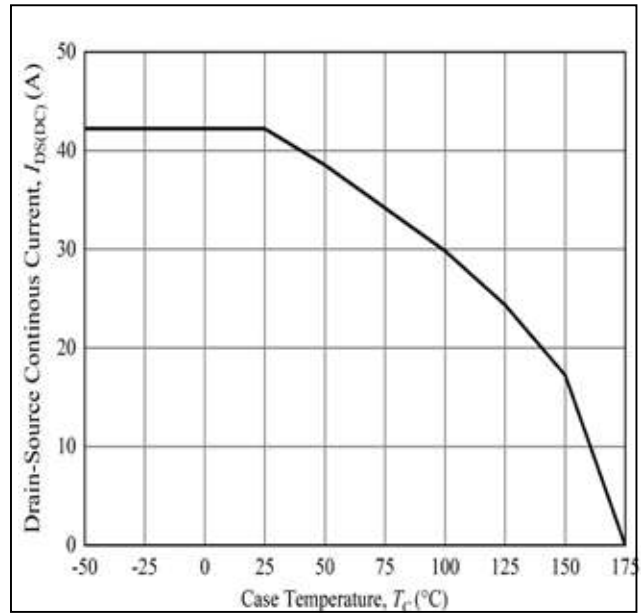


Figure 18: Continuous Drain Current Derating Curve

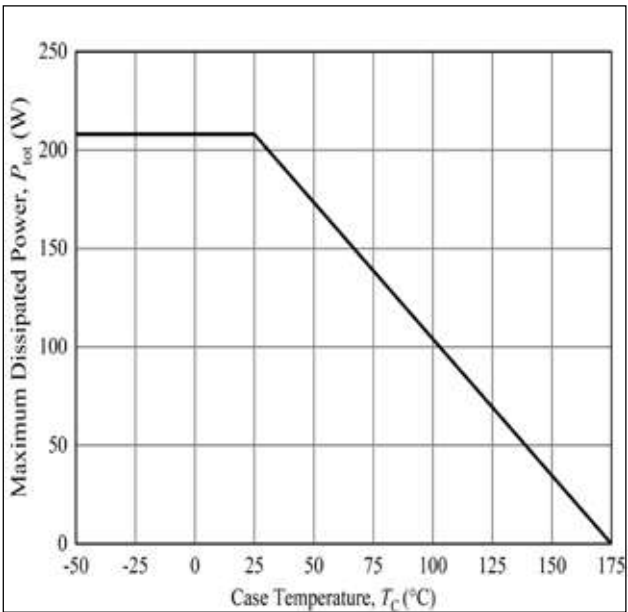


Figure 19: Power Dissipation Derating Curve

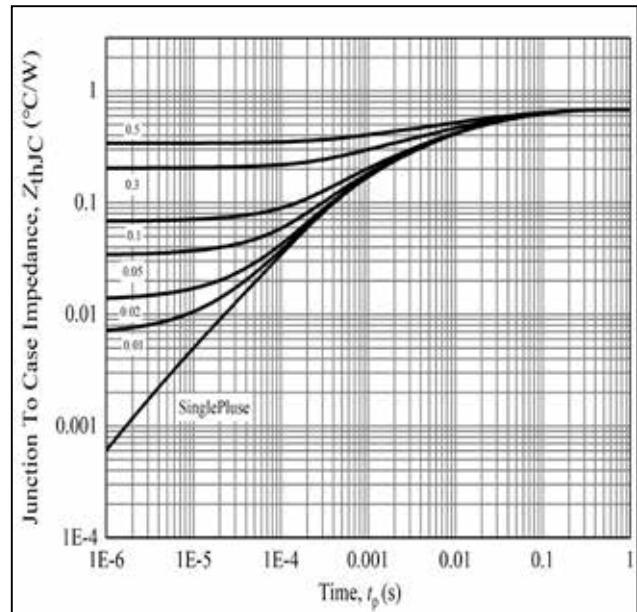


Figure 20: Typical Transient Thermal Impedance (Junction – Case) with Duty Cycle

Typical Performance

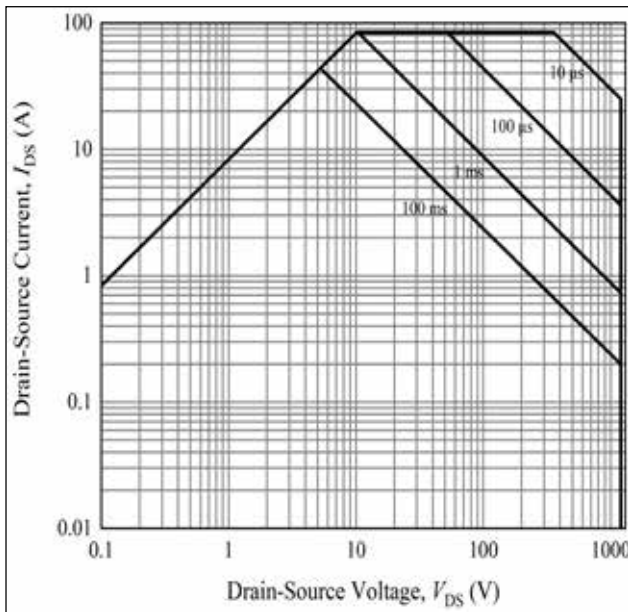


Figure 21: Safe Operate Area

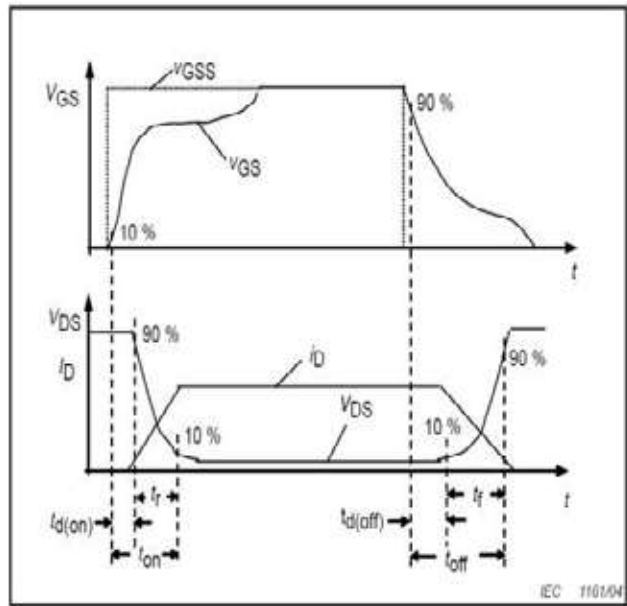


Figure 22: Resistive Switching Time Description

Test Circuit Schematic

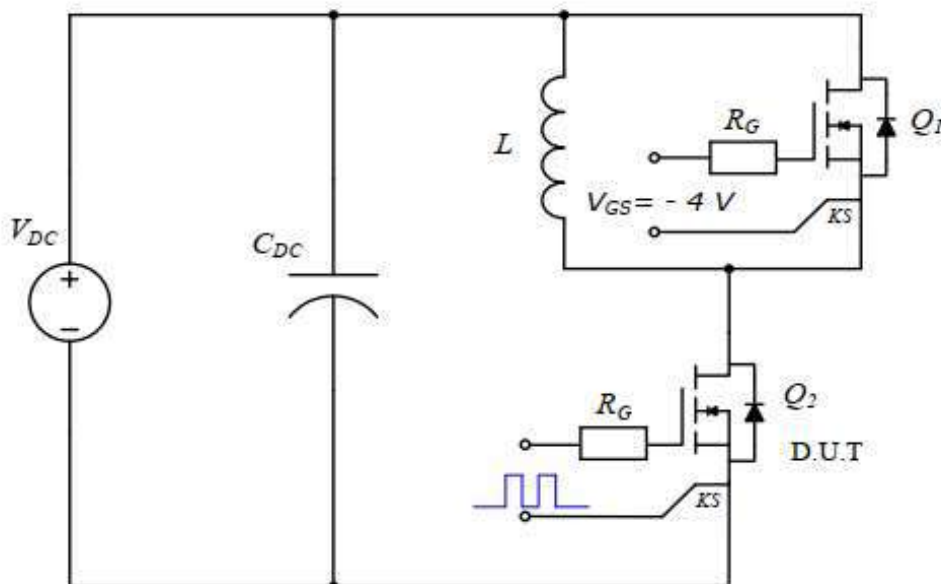
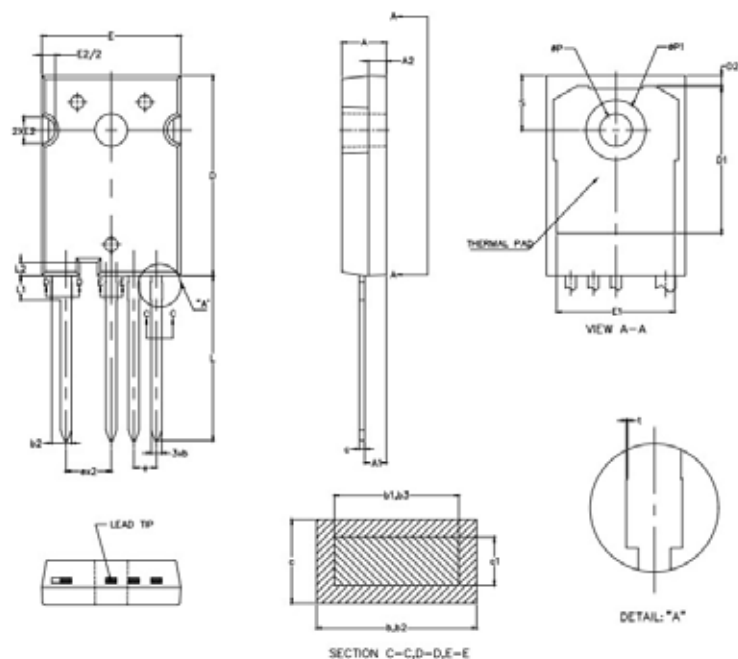


Figure 23: Clamped Inductive Switching Waveform Test Circuit

Package Dimensions

Package TO-247-3



DIMENSIONS	DIMENSIONS			
	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.15	1.22	0.045	0.048
b2	2.16	2.26	0.085	0.089
b3	2.15	2.22	0.085	0.087
c	0.59	0.66	0.023	0.026
c1	0.58	0.62	0.023	0.024
D	22.40	22.60	0.882	0.890
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.75	15.90	0.620	0.626
E1	13.26	—	0.552	—
E2	2.90	3.10	0.114	0.122
e	2.54BSC		0.1BSC	
L	18.30	18.60	0.720	0.732
L1	—	2.80	—	0.110
L2	—	1.50	—	0.059
øP	3.50	3.70	0.138	0.146
øP1	—	7.40	—	0.291
S	6.05	6.25	0.238	0.246
t	0.00	0.15	0.000	0.006

Revision History

Document Version	Description of Changes
Rev.1.0	Released
Rev.2.0	Static parameters at different temperatures are added

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